PCN Numbe	20160606003						PCN Date:		te:	06/21/2016			
Title: Qu	Assembly Material set for Selected Device(s)												
Customer C	Customer Contact: PCN Manager Dept: Quality Services												
Proposed 1 ^s			09/21				•	d Sample Availability		Date provided at			
-			1	/ -	-						•	sam	ple request
Change Typ			Design Wafer Bump Site										
	y Process							Wafer Bump Material					
	y Materials			\exists		number cl	hange						
	cal Specific					Site				Wafer Bump Process Wafer Fab Site			
	Shipping/L		ng		Test	Process				Wafer Fab Materials		erials	
										Wafer	Fat	o Pro	cess
					PC	CN Detai	ls						
Description	of Change	e:											
Texas Instruments is pleased to announce the qualification of new assembly material for devices listed in "Product affected" section below. Devices will remain in current assembly facility and piece part changes as follows:													
	Materia	al				Current			Proposed				
Wire (0.80, 0.96, 1.15mils Au			0.96mils Cu						
	rame thick			10 mils			10mils, 6mils						
	compound	1		4042500			4147858						
Mold	compound			4205694				4211880					
Reason for	Change:												
Continuity of supply. 1) To align with world technology trends and use assembly materials with enhanced mechanical and electrical properties 2) Maximize flexibility within our Assembly/Test production sites.													
Anticipated	impact or	Fit,	Form,	Fu	nctio	on, Quality	or Rel	liabi	lity	(posit	tive	/ ne	egative):
None.													
Anticipated	Anticipated impact on Material Declaration												
 No Impact to the Material Declaration Material Declarations or Product Content reports are driven from production data and will be available following the production release. Upon production release the revised reports can be obtained from the <u>TI ECO website</u>. 						production							
Changes to product identification resulting from this PCN:													
None.													
Product Affected:													
Please see page two of this document for your list of PCN affected devices.													

Qualification Report

Universal BOM Mold 4211880 and Die Attach 4147858 for SOIC DW Packages in TITL and MLA Approve Date 12-May-2016

Attributes	Qual Device: ADS1213U	Qual Device: ADS820U	Qual Device: ADS8504IBDW	Qual Device: MSP430F123IDWR	Qual Device: SN65LBC170DW		
Assembly Site	TAI	TAI	TAI	TAI	MLA		
Package Family	SOIC	SOIC	SOIC	SOIC	SOIC		
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0		
Wafer Fab Supplier	ОКІ	TSMC WF2	DMOS5	TSMC	DFAB		
Wafer Fab Process	OKIDALSATFAB_BICMOS	0.60UM-TSMC	50HPA07	0.35UM-TSMC	LBC3S		

Product Attributes

Attributes	Qual Device: SN65LBC170DW_SSTN	Qual Device: SN74LVC541ADW	Qual Device: SN74LVC541ADW_SSTN	QBS Package Reference: TL494IDR	QBS Package Reference: ULQ2003AQDRQ1
Assembly Site	MLA	MLA	MLA	FMX	FMX
Package Family	SOIC	SOIC	SOIC	SOIC	SOIC
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V0	UL 94 V-0
Wafer Fab Supplier	DFAB	FFAB	FFAB	SFAB	SFAB
Wafer Fab Process	LBC3S	ASLC10	ASLC10	JI1	JI1-SLM

- QBS: Qual By Similarity

- Qual Devices qualified at LEVEL1-260C: SN65LBC170DW, SN74LVC541ADW, MSP430F123IDWR, TL494IDR, ULQ200AQDRQ1

- Qual Devices qualified at LEVEL2-260C: ADS1213U, ADS8504IBDW, ADS820U

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: ADS1213U	Qual Device: ADS820U	Qual Device: ADS8504IBDW	Qual Device: MSP430F123ID WR	Qual Device: SN65LBC170D W
AC	Autoclave 121C	96 Hours	1/77/0	-	1/77/0	1/77/0	1/77/0
ED	Electrical Characterization, side by side	Per datasheet parameters	Pass	Pass	Pass	-	Pass
HAST	Biased HAST, 130C/85%RH	192 Hours	-	-	-	-	-
HAST	Biased HAST, 130C/85%RH	96 Hours	-	-	-	-	-
HTSL	High Temp Storage Bake 170C	420 Hours	1/77/0	-	1/77/0	1/77/0	1/77/0
MQ	Manufacturability (Assembly)	(per mfg. Site specification)	Pass	Pass	Pass	Pass	Pass
тс	Temperature Cycle, -65/150C	500 Cycles	1/77/0	3/231/0	1/77/0	1/77/0	1/77/0

Туре	Test Name / Condition	Duration	Qual Device: SN65LBC170 DW_ SSTN	Qual Device: SN74LVC541A DW	Qual Device: SN74LVC541A DW_SSTN	QBS Package Reference: TL494IDR	QBS Package Reference: ULQ2003AQDR Q1_STDLF
AC	Autoclave 121C	96 Hours	3/231/0	3/231/0	3/231/0	-	3/231/0
ED	Electrical Characterization, side by side	Per datasheet parameters	Pass	Pass	Pass	-	-
HAST	Biased HAST, 130C/85%RH	192 Hours	-	-	-	3/231/0	3/217/0
HAST	Biased HAST, 130C/85%RH	96 Hours	-	-	-	3/231/0	3/231/0
HTSL	High Temp Storage Bake 170C	420 Hours	3/231/0	3/231/0	3/231/0	-	-
MQ	Manufacturability (Assembly)	(per mfg. Site specification)	Pass	Pass	Pass	-	-
TC	Temperature Cycle, -65/150C	500 Cycles	3/231/0	3/231/0	3/231/0	-	3/231/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

Qualification Report

SOIC-DW 6 mil thick, 2X12 HD, TIM Leadframe Qualification Approve Date 12-May-2016

Product Attributes Qual Device: **Qual Device:** Qual Device: Qual Device: Attributes SN65LBC170DW_SSROUGH SN65LBC170DW_STD_AU SN74LVC541ADW_SSROUGH SN74LVC541ADW_STD_AU Assembly TIM ΤΙΜ ΤΙΜ ТІМ Site Package SOIC SOIC SOIC SOIC Family Flammability UL 94 V-0 UL 94 V-0 UL 94 V-0 UL 94 V-0 Rating Wafer Fab DFAB DFAB FFAB FFAB Supplier Wafer Fab LBC3S LBC3S A3C10TLM A3C10TLM Process

- QBS: Qual By Similarity

- Qual Devices qualified at LEVEL1-260CG: SN65LBC170DW, SN74LVC541ADW

Qualification Results

	Qualification Results								
	Data Displayed as: Number of lots / Total sample size / Total failed								
Туре	Test Name / Condition	Duration	Qual Device: SN65LBC170DW_ SSROUGH	Qual Device: SN65LBC170DW_ STD_AU	Qual Device: SN74LVC541ADW_ SSROUGH	Qual Device: SN74LVC541ADW_ STD_AU			
AC	Autoclave 121C	96 Hours	3/231/0	1/77/0	3/231/0	3/231/0			
HTSL	High Temp Storage Bake 170C	420 Hours	3/231/0	1/77/0	3/231/0	3/231/0			
LI	Lead Fatigue	Leads	3/66/0	-	-	-			
LI	Lead Pull	Leads	3/66/0	-	-	-			
MQ	Manufacturability (Assembly)	(per mfg. Site specification)	Pass	Pass	Pass	Pass			
PD	Physical Dimensions	(per mechanical drawing)	3/15/0	-	-	-			
SD	Solderability	8 Hours Steam Age, Pb free	3/66/0	-	-	-			
тс	Temperature Cycle, - 65/150C	500 Cycles	3/231/0	1/77/0	3/231/0	3/231/0			

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

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USA	PCNAmericasContact@list.ti.com
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